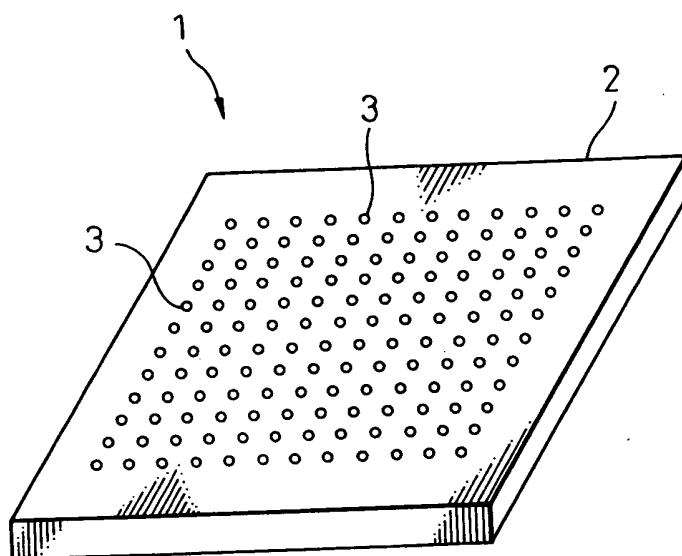


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Fig.1



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Fig. 2

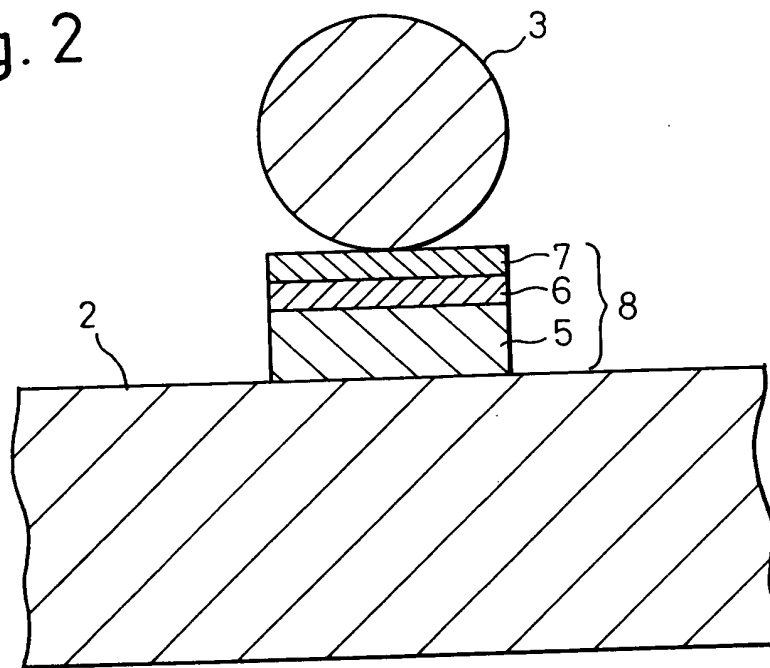


Fig. 3

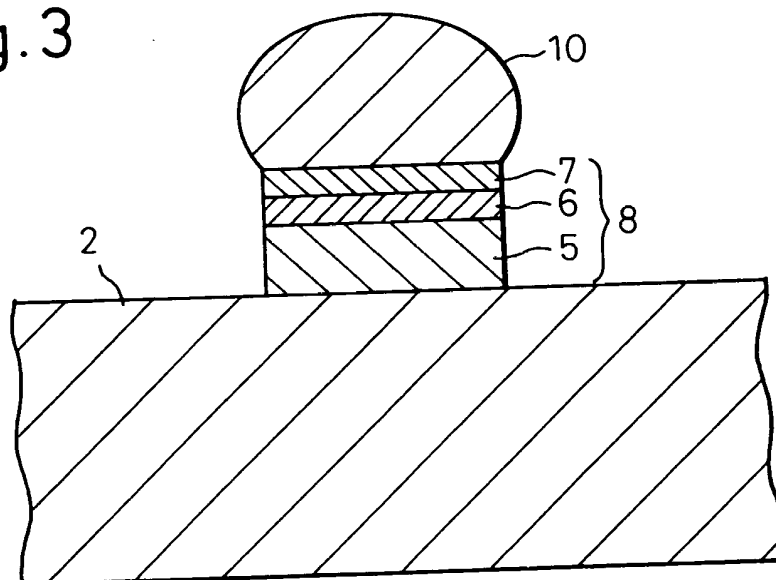


Fig. 4 is a cross-sectional view of a semiconductor device. It shows a substrate 41 with a layer 42 on top. A central block 45 is positioned on layer 42, with side regions 44 on either side. A circular feature 46 is positioned above the central block 45. A layer 43 is shown on the right side of the device.

This diagram shows a cross-sectional view of a second embodiment of the device. It features a base layer 41 with a top surface 42. A second substrate 43 is positioned on top of the base layer. A second conductive layer 44 is formed on the top surface of the second substrate 43. A second conductive pad 45 is formed on the second conductive layer 44. A second conductive pad 47 is formed on the top surface of the second substrate 43, positioned adjacent to the second conductive pad 45. The second conductive pad 47 is formed on a second conductive layer 46, which is formed on the top surface of the second substrate 43.

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Fig. 5

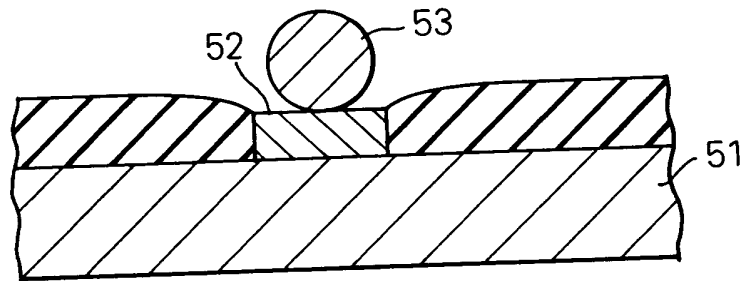


Fig. 6A

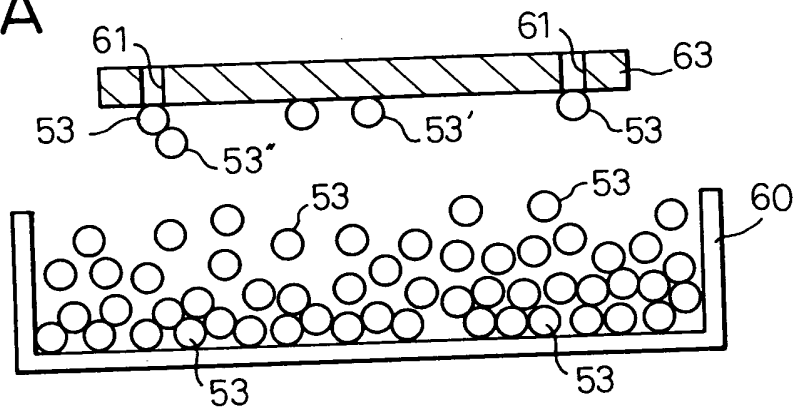


Fig. 6B

